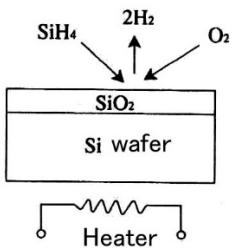
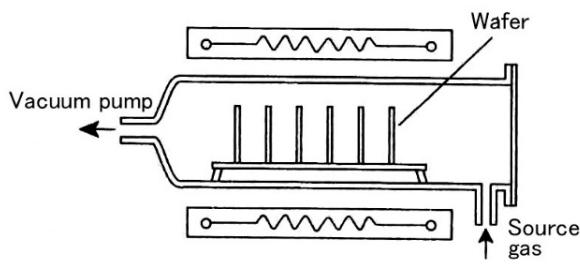


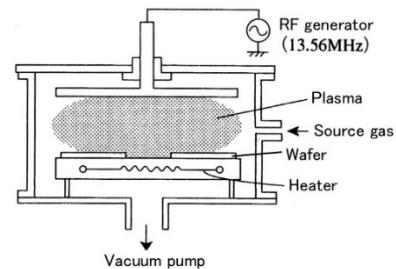
## 4 Chemical vapor deposition (CVD) and RF induction heating



Principle of chemical vapor deposition



Low pressure (LP) CVD



Plasma CVD

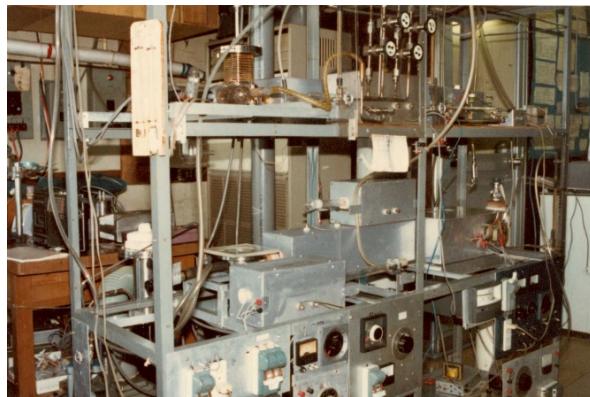
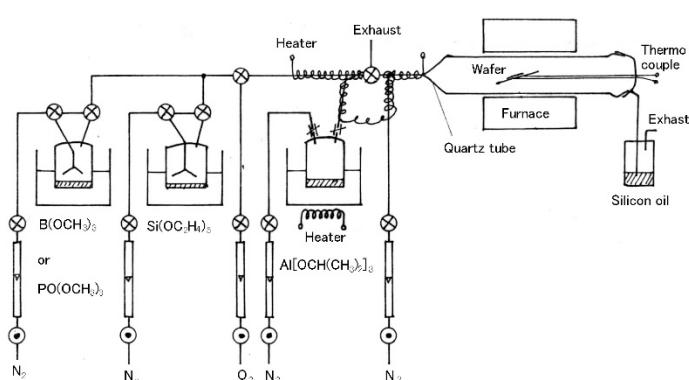


RF heating poly Si, SiO<sub>2</sub> CVD (top)

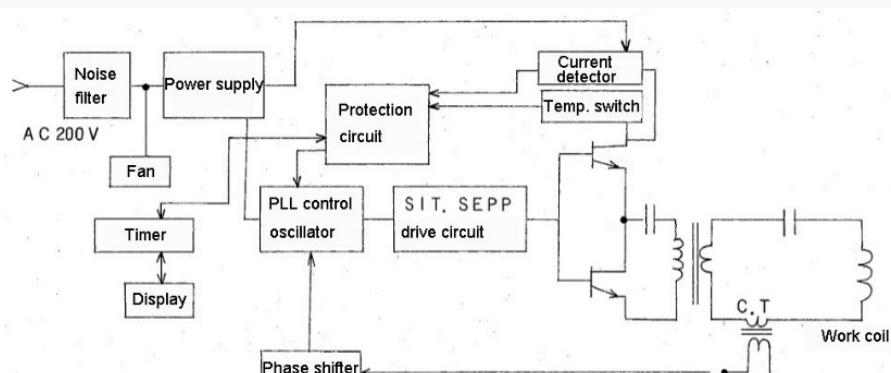
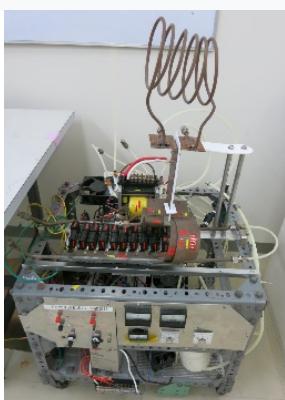


Low temperature SiO<sub>2</sub>CVD (exhibited)

Infrared heating Al<sub>2</sub>O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> CVD (bottom)



Organic liquid source (Tetraethoxysilane TEOS etc.) P<sub>2</sub>O<sub>5</sub>-SiO<sub>2</sub>, B<sub>2</sub>O<sub>3</sub>-SiO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>-SiO<sub>2</sub> CVD



Oscillator for RF inductive heating using SIT (static induction transistor) (Tokin)(exhibited)